EMC COMPO 2019
21-23, October
Haining, Hangzhou

12th International Workshop on the
Electromagnetic Compatibility of Integrated Circuits

EMC Compo 2019
in Haining, Hangzhou, China

October 21-23, 2019 Haining, Hangzhou, China www.emcconf.org | www.emccompo.org

Call for Papers

The achievement in terms of operating frequency and integration of semiconductor technology are constantly creating new challenges in IC EMC, which must necessarily be addressed at both integrated circuits and system level. Keeping up-to-date is of paramount importance to be successful in this field. Since the inception of the 1st International IC EMC Workshop in Toulouse, France, in 1999, it has been held various at Europe and one time in Japan, **The 12th EMC COMPO will be held in Haining, Hongzhou**, a most advanced electronic industry and research hub located at the Yangtze Delta and Shanghai Industry Zone.

EMC Compo is the first time to be held in China. The workshop will presents the state-of-arts on IC EMC related issues, not only fundamental improvements in modeling and measurement, but also novel design methodologies and standards. A Technical Exhibition will provide tool and equipment manufacturers and suppliers an opportunity to display their products and services to potential clients.

Publication at IEEE Transaction EMC: All authors attended this conference will be invited to submit extended paper for possible publication in a Special Session of IEEE Trans on EMC. In addition, all eligible papers will be submitted for online publication at the IEEE Xplore Digital library.

Please prepare come to this unique workshop and conference, presents your latest development, meet international colleagues, learn from experts, find collaborators.

Symposium Topics

- Artificial Intelligence in IC EMC
- Design of 2D and 3D system-on-chip (SoC) for EMC
- Hardware-software co-design and integration for IC EMC
- Emission and immunity-aware IC design
- ESD immunity techniques at IC level
- Signal and power integrities at IC level
- Combined effects of radiation and aging on IC EM sensitivity
- Harsh environment effects on IC EM sensitivity
- IC EMC for avionics and automotive applications
- EMC-aware analog and mixed signal circuits
- RF ICs EMC
- IC-level measurement techniques for EMC
- IC-level modeling techniques for EMC
- EMC simulation of ICs
- EMC in microwave ICs
- EMC-aware software solutions
- FPGA-based embedded systems and EMC

Important Dates

Item	Date
▪ Preliminary paper submission(3 pages in PDF) ▪ Abstract submission (500 words to 1-page) ▪ Tutorial /workshop proposal	12 July. 2019
▪ Notification of review feedback	16 Aug. 2019
▪ Final paper Due	05 Sept. 2019
▪ Submission of extended version to IEEE Trans EMC	28 Feb. 2020

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